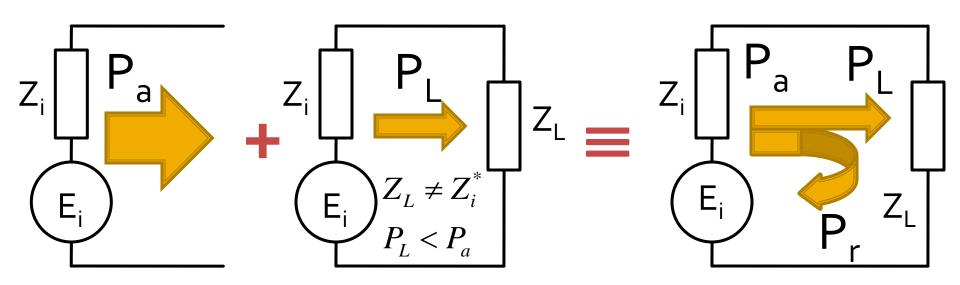
Laboratory 3 (w7-8) 2021/2022

## **Microwave Devices and Circuits**

# **Short theory**

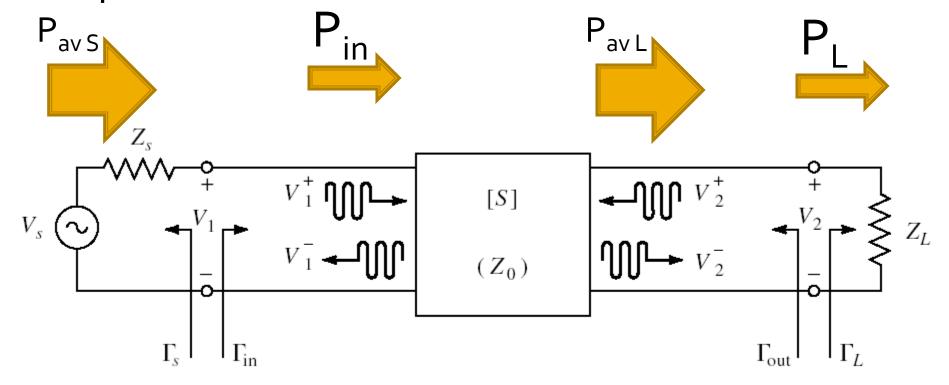
#### Reflection and power / Model



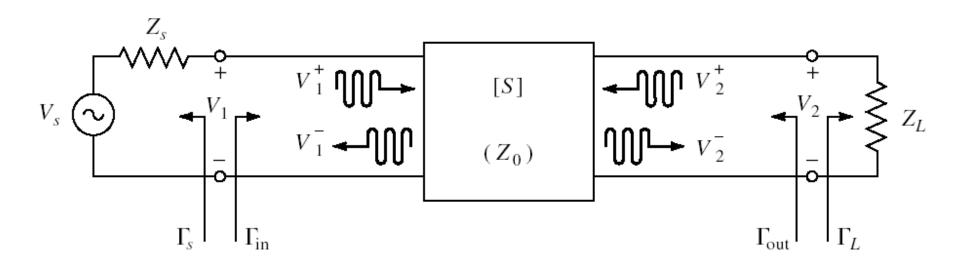
- The source has the ability to sent to the load a certain maximum power (available power) P<sub>a</sub>
- For a particular load the power sent to the load is less than the maximum (mismatch) P<sub>L</sub> < P<sub>a</sub>
- The phenomenon is "as if" (model) some of the power is reflected P<sub>r</sub> = P<sub>a</sub> P<sub>l</sub>
- The power is a scalar!

### Power / Matching

 Two ports in which matching influences the power transfer

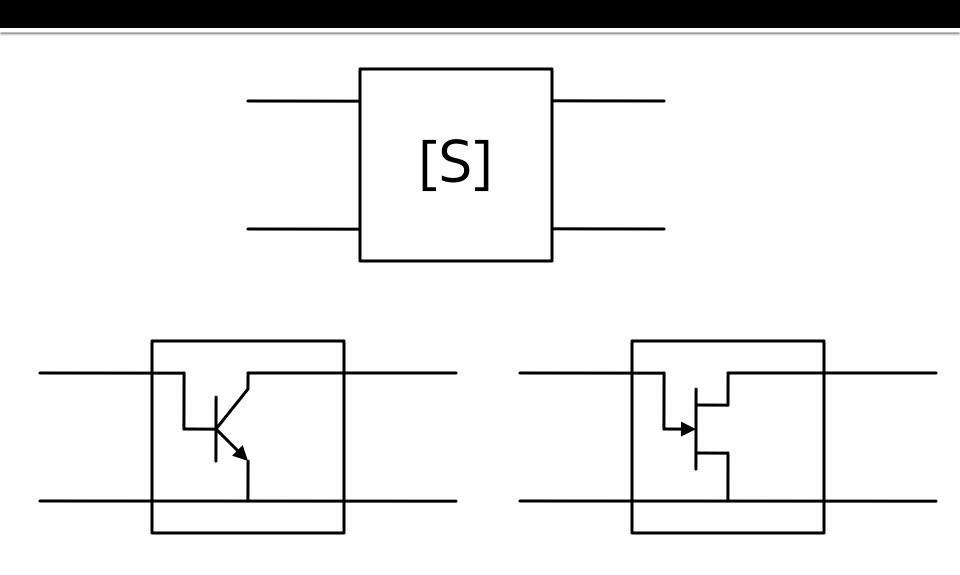


#### Amplifier as two-port

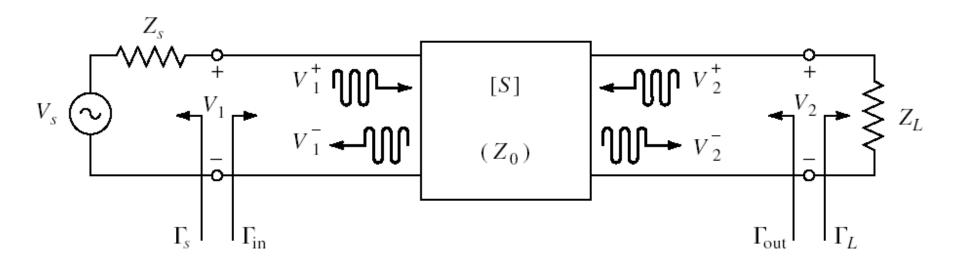


- Charaterized with S parameters
- normalized at Zo (implicit 5οΩ)
- Datasheets: S parameters for specific bias conditions

## **S** parameters



#### Amplifier as two-port



- For an amplifier two-port we are interested in:
  - stability
  - power gain
  - noise (sometimes small signals)
  - linearity (sometimes large signals)

#### **Stability**

$$\left| \Gamma_{in} \right| < 1$$
  $\left| S_{11} + \frac{S_{12} \cdot S_{21} \cdot \Gamma_L}{1 - S_{22} \cdot \Gamma_L} \right| < 1$ 

 We can calculate conditions to be met by Γ<sub>L</sub> to achieve stability

$$\left| \Gamma_{out} \right| < 1$$
  $\left| S_{22} + \frac{S_{12} \cdot S_{21} \cdot \Gamma_{S}}{1 - S_{11} \cdot \Gamma_{S}} \right| < 1$ 

• We can calculate conditions to be met by  $\Gamma_s$  to achieve stability

## Output stability circle (CSOUT)

$$\left| \Gamma_{L} - \frac{\left( S_{22} - \Delta \cdot S_{11}^{*} \right)^{*}}{\left| S_{22} \right|^{2} - \left| \Delta \right|^{2}} \right| = \left| \frac{S_{12} \cdot S_{21}}{\left| S_{22} \right|^{2} - \left| \Delta \right|^{2}} \right| \qquad \left| \Gamma_{L} - C_{L} \right| = R_{L}$$

- We obtain the equation of a circle in the complex plane, which represents the locus of  $\Gamma_L$  for the limit between stability and instability ( $|\Gamma_{in}| = 1$ )
- This circle is the **output stability circle**  $(\Gamma_L)$

$$C_{L} = \frac{\left(S_{22} - \Delta \cdot S_{11}^{*}\right)^{*}}{\left|S_{22}\right|^{2} - \left|\Delta\right|^{2}} \qquad R_{L} = \frac{\left|S_{12} \cdot S_{21}\right|}{\left|\left|S_{22}\right|^{2} - \left|\Delta\right|^{2}\right|}$$

## Input stability circle (CSIN)

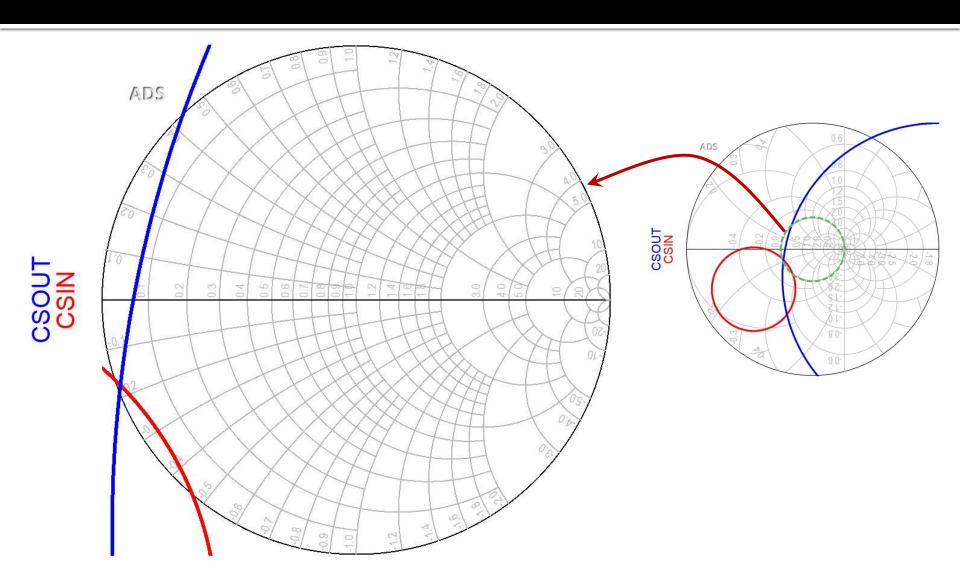
Similarly 
$$|\Gamma_{out}| = 1$$

$$\left| S_{22} + \frac{S_{12} \cdot S_{21} \cdot \Gamma_S}{1 - S_{11} \cdot \Gamma_S} \right| = 1$$

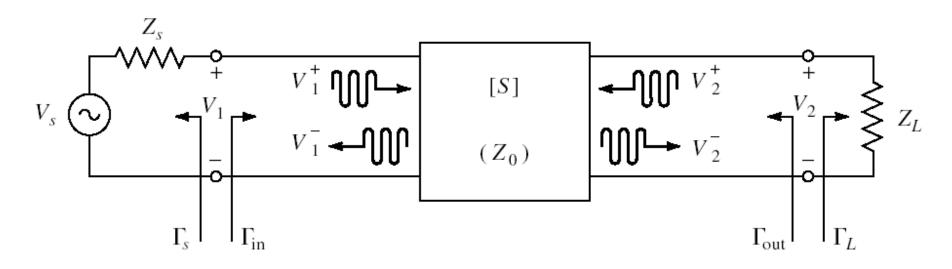
- We obtain the equation of a circle in the complex plane, which represents the locus of  $\Gamma_S$  for the limit between stability and instability ( $|\Gamma_{out}| = 1$ )
- This circle is the **input stability circle** ( $\Gamma_S$ )

$$C_{S} = \frac{\left(S_{11} - \Delta \cdot S_{22}^{*}\right)^{*}}{\left|S_{11}\right|^{2} - \left|\Delta\right|^{2}} \qquad R_{S} = \frac{\left|S_{12} \cdot S_{21}\right|}{\left|\left|S_{11}\right|^{2} - \left|\Delta\right|^{2}\right|}$$

#### **ADS**



### Amplifier as two-port



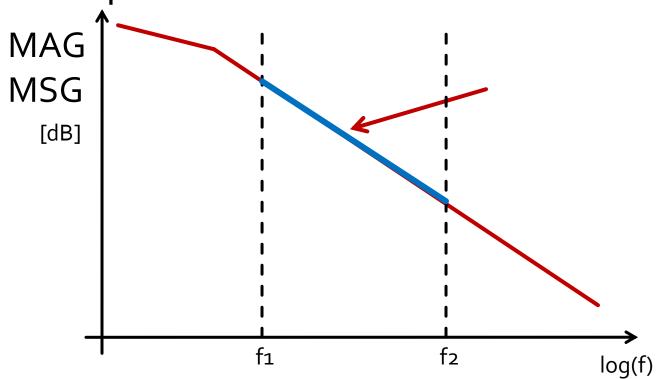
- For an amplifier two-port we are interested in:
  - stability
  - power gain
  - noise (sometimes small signals)
  - linearity (sometimes large signals)

#### Design for Specified Gain

- In many cases we need an approach other than "brute force" when we prefer to design for less than the maximum obtainable gain, in order to:
  - improve noise behavior (L<sub>3</sub> + C<sub>9</sub>)
  - improve stability
  - improve VSWR
  - control performance at multiple frequencies
  - improve amplifier's bandwidth

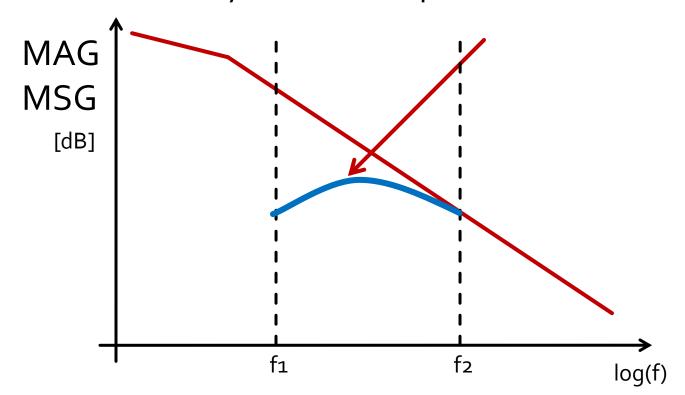
#### Wide bandwidth amplifier

 Design for maximum gain at two different frequencies creates an frequency unbalanced amplifier

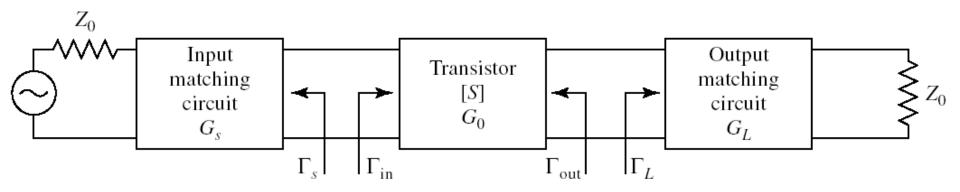


#### Wide bandwidth amplifier

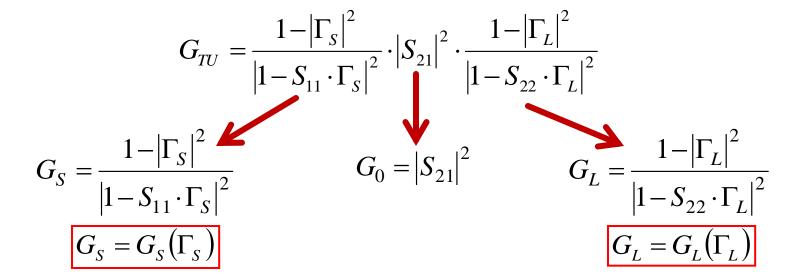
- Design for maximum gain at highest frequency
- Controlled mismatch at lower frequency
  - eventually at more frequencies inside the bandwidth



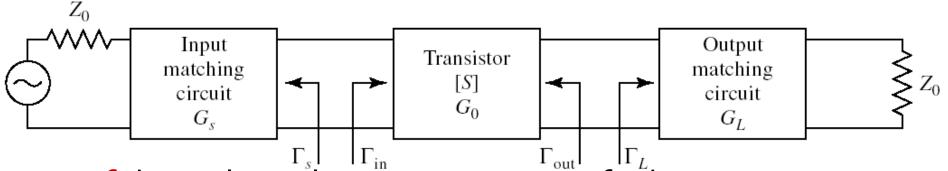
## Design for Specified Gain



In the unilateral assumption:



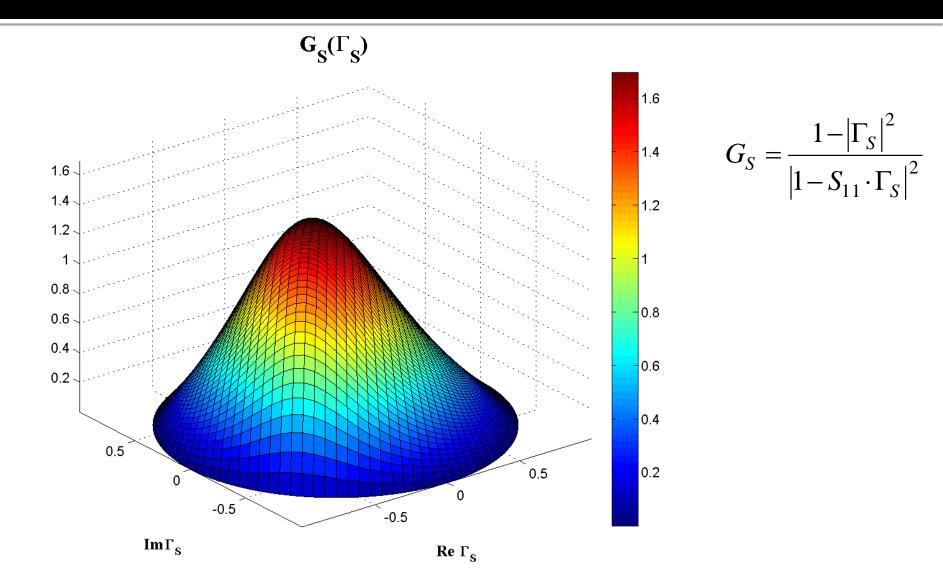
### Design for Specified Gain



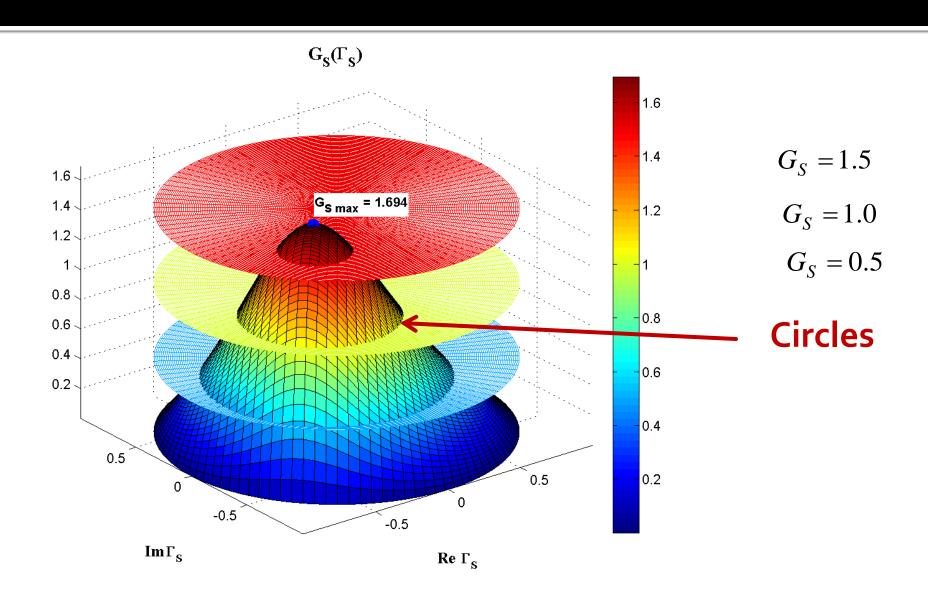
- If the unilateral assumption is justified:
  - power gain added by the input matching circuit is not influenced by the output matching circuit  $G_S = G_S(\Gamma_S)$
  - power gain added by the output matching circuit **is not** influenced by the input matching circuit  $G_{I} = G_{I}(\Gamma_{I})$
- Output /Input match can be designed independently
  - We can impose different demands for input/output
  - Total gain is:

$$G_T = G_S \cdot G_0 \cdot G_L \qquad G_T [dB] = G_S [dB] + G_0 [dB] + G_L [dB]$$

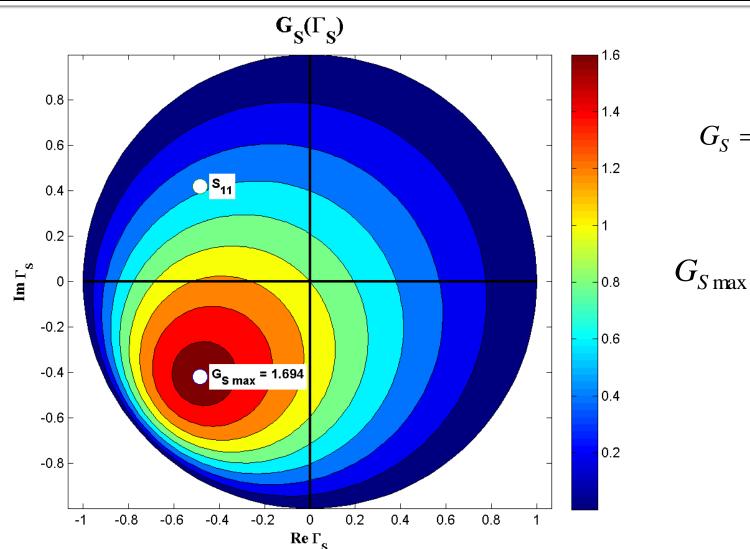
## $G_S(\Gamma_S)$



# $G_S(\Gamma_S)$ , constant value contours



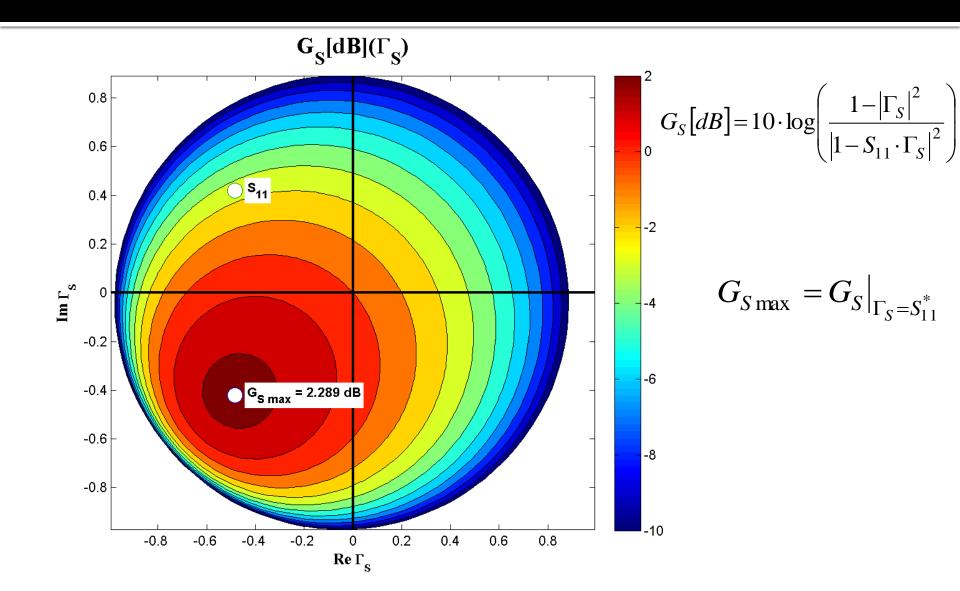
## $G_s(\Gamma_s)$ , constant value contours



$$G_S = \frac{1 - \left| \Gamma_S \right|^2}{\left| 1 - S_{11} \cdot \Gamma_S \right|^2}$$

$$G_{S \max} = G_S \big|_{\Gamma_S = S_{11}^*}$$

#### $G_s[dB](\Gamma_s)$ , constant value contours



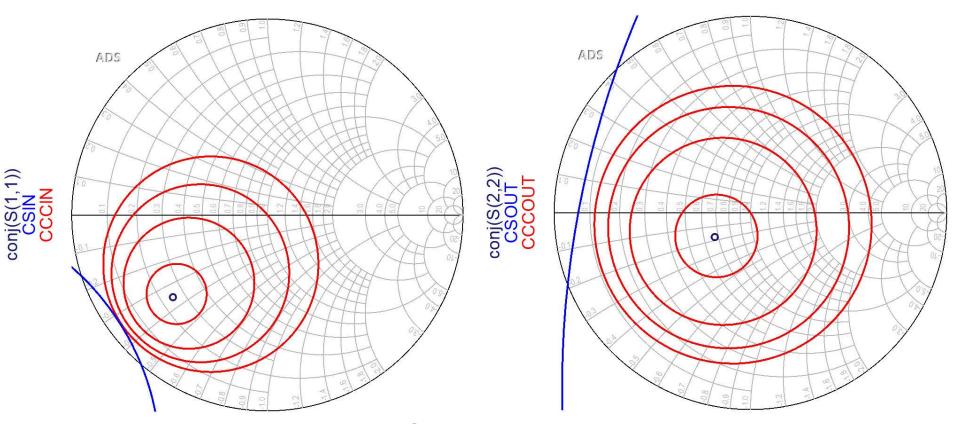
#### Input section constant gain circles

$$\begin{vmatrix}
\Gamma_{S} - \frac{g_{S} \cdot S_{11}^{*}}{1 - (1 - g_{S}) \cdot |S_{11}|^{2}} | = \frac{\sqrt{1 - g_{S}} \cdot (1 - |S_{11}|^{2})}{1 - (1 - g_{S}) \cdot |S_{11}|^{2}} \qquad |\Gamma_{S} - C_{S}| = R_{S}$$

$$C_{S} = \frac{g_{S} \cdot S_{11}^{*}}{1 - (1 - g_{S}) \cdot |S_{11}|^{2}} \qquad R_{S} = \frac{\sqrt{1 - g_{S}} \cdot (1 - |S_{11}|^{2})}{1 - (1 - g_{S}) \cdot |S_{11}|^{2}}$$

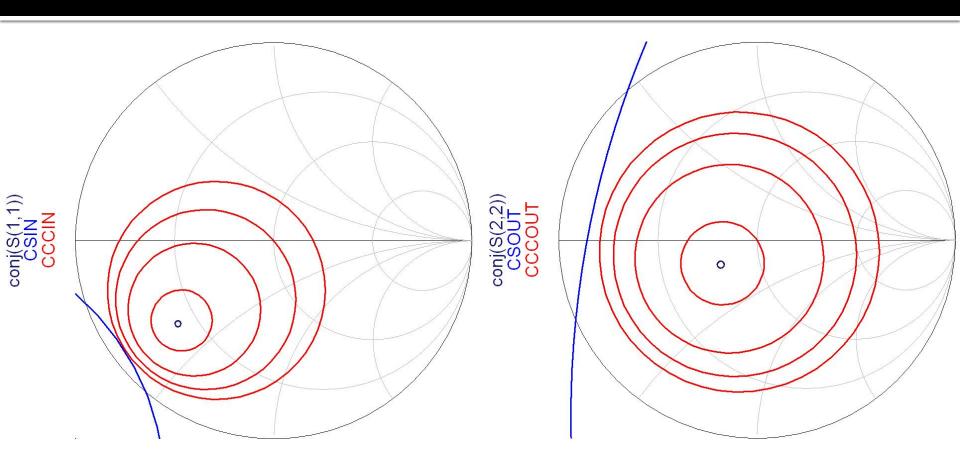
- Equation of a circle in the complex plane where Γ<sub>s</sub> is plotted
- Interpretation: Any reflection coefficient Γ<sub>S</sub> which plotted in the complex plane lies on the circle drawn for g<sub>circle</sub> = G<sub>circle</sub>/G<sub>Smax</sub> will lead to a gain G<sub>S</sub> = G<sub>circle</sub>
  - Any reflection coefficient  $\Gamma_S$  plotted **outside** this circle will lead to a gain  $G_S < G_{circle}$
  - Any reflection coefficient  $\Gamma_S$  plotted **inside** this circle will lead to a gain  $G_S > G_{circle}$
- Similar discussion for output port (Γ<sub>L</sub>) CCCIN/CCCOUT

#### CCCIN, CCCOUT



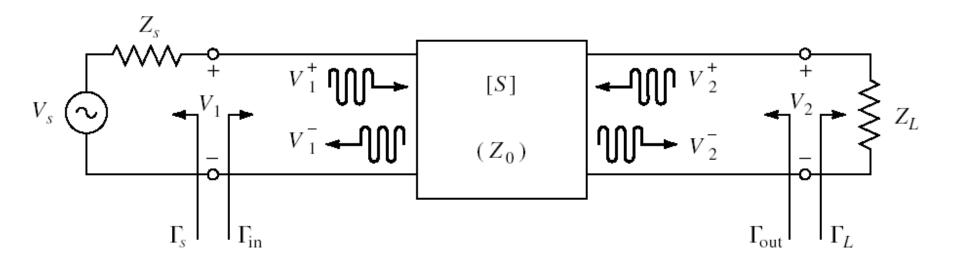
- Circles are plotted for requested values (in dB!)
   It is usefull to compute G<sub>Smax</sub> and G<sub>Lmax</sub> before
- - in order to request relevant circles

### CCCIN, CCCOUT



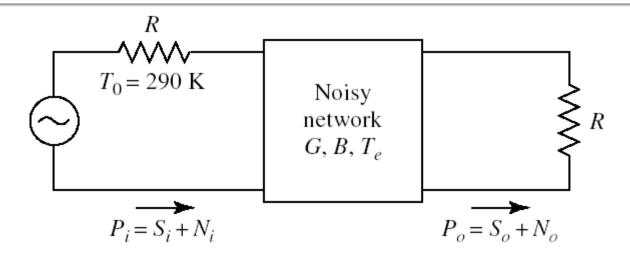
- Cercurile se reprezinta pentru valorile cerute in dB
- Este utila calcularea G<sub>Smax</sub> si G<sub>Lmax</sub> anterior

#### Amplifier as two-port



- For an amplifier two-port we are interested in:
  - stability
  - power gain
  - noise (sometimes small signals)
  - linearity (sometimes large signals)

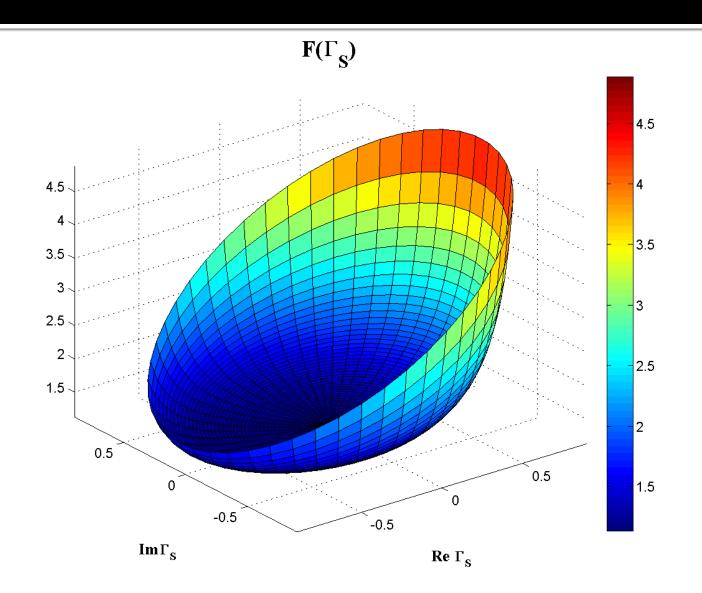
### Noise Figure F



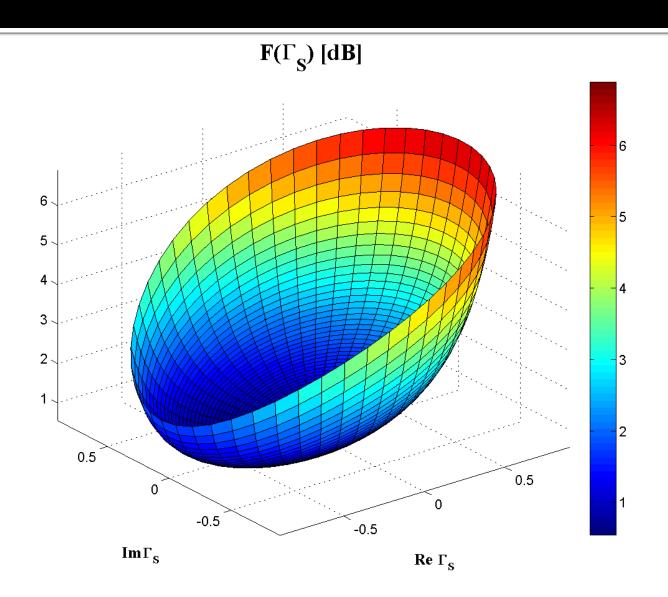
 The noise figure F, is a measure of the reduction in signal-to-noise ratio between the input and output of a device

$$F = \frac{S_i/N_i}{S_o/N_o}\bigg|_{T_0 = 290K}$$

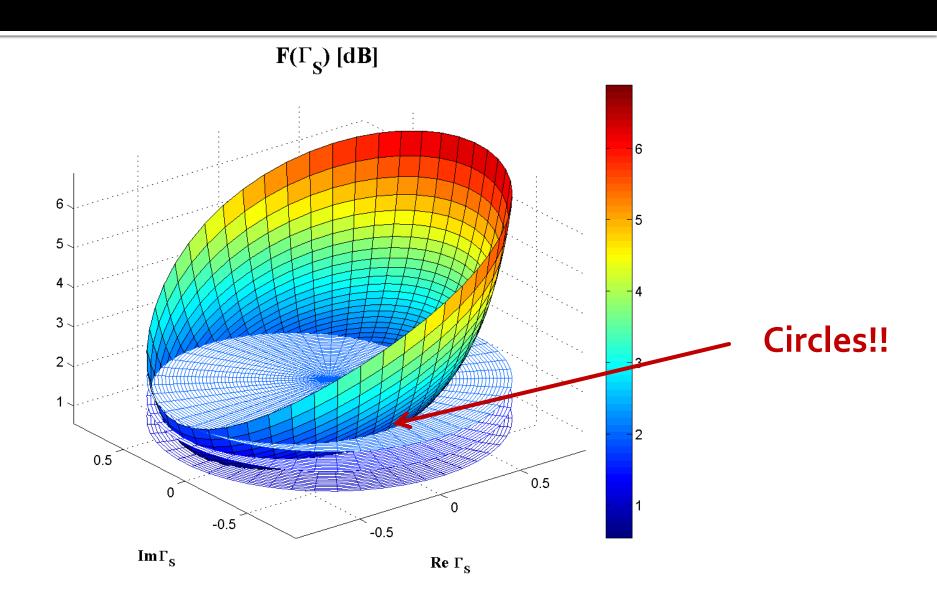
#### $F(\Gamma_S)$



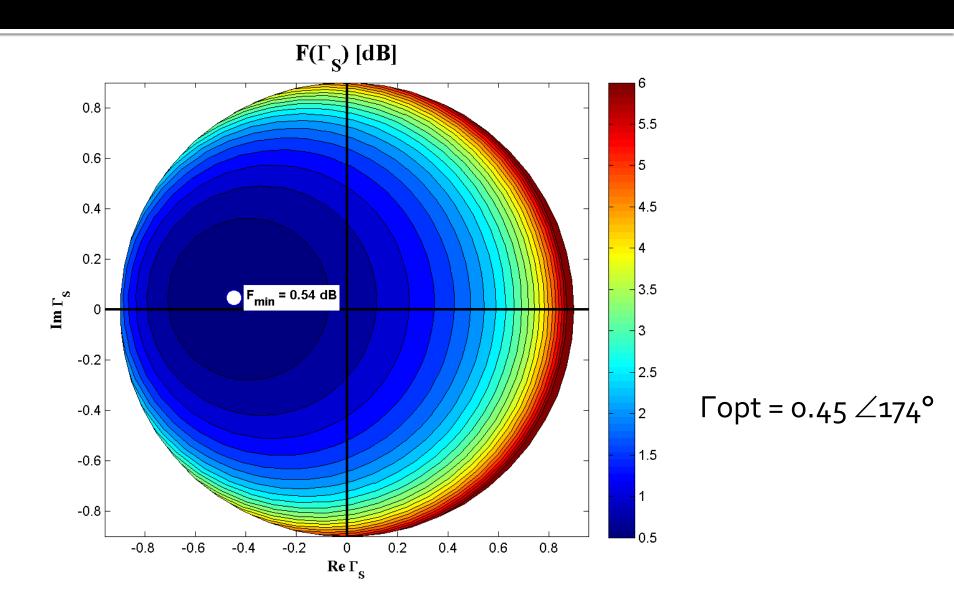
# $F[dB](\Gamma_S)$



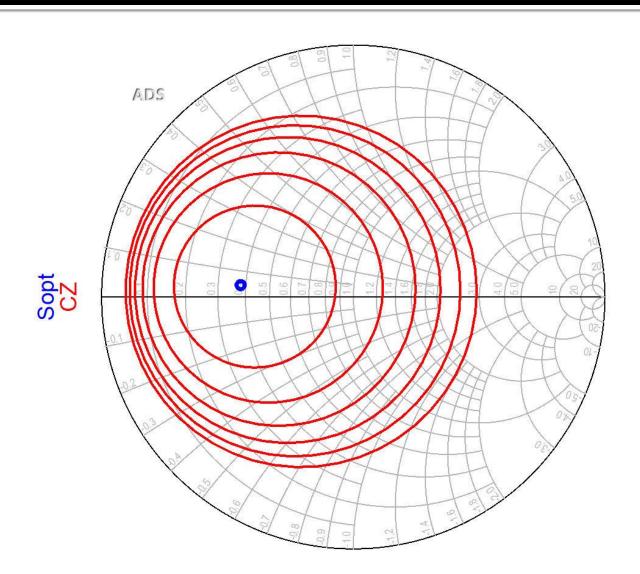
#### $F[dB](\Gamma_S)$ , constant value contours



#### $G_s[dB](\Gamma_s)$ , constant value contours



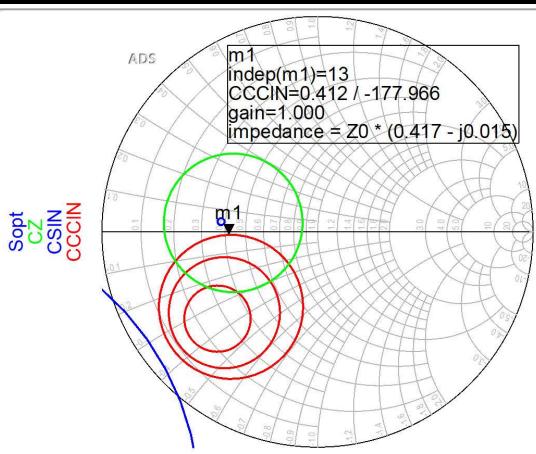
## CZ – Noise Circle (input port only!)



#### Example, LNA @ 5 GHz

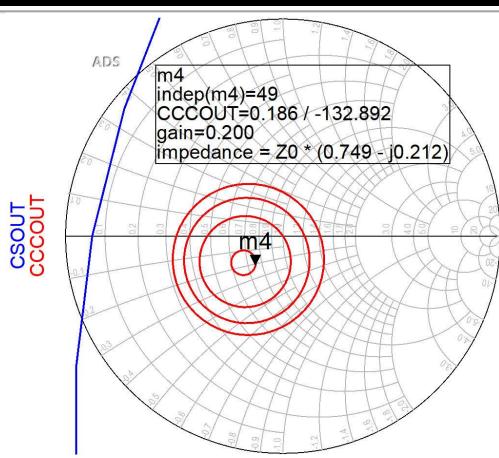
- Low Noise Amplifier
- At the input port we must compromise between
  - noise (input constant noise circle CZ)
  - power gain (input constant gain circle CCCIN)
  - stability (input stability circle CSIN)
- At the output port noise does not intervene (no influence). The compromise is between:
  - power (output constant gain circle CCCOUT)
  - stability (output stability circle CSOUT)

# Input matching circuit



- If we can afford a 1.2dB decrease of the input gain for better NF,Q (Gs = 1 dB), position m1 above is better
- We obtain better (smaller) NF

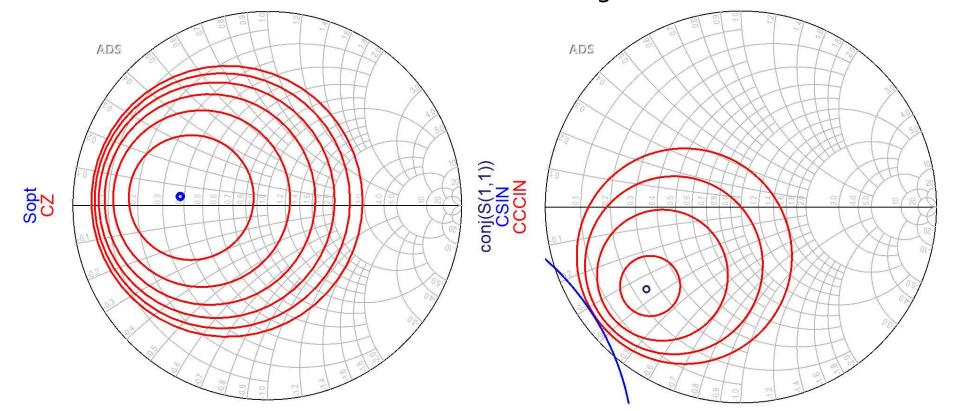
# Output matching circuit



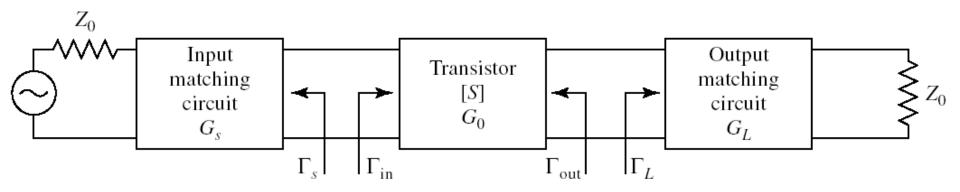
- output constant gain circles CCCOUT: -0.4dB, -0.2dB, odB, +0.2dB
- The lack of noise restrictions allows optimization for better gain (close to maximum – position m4)

### LNA – Low Noise Amplifier

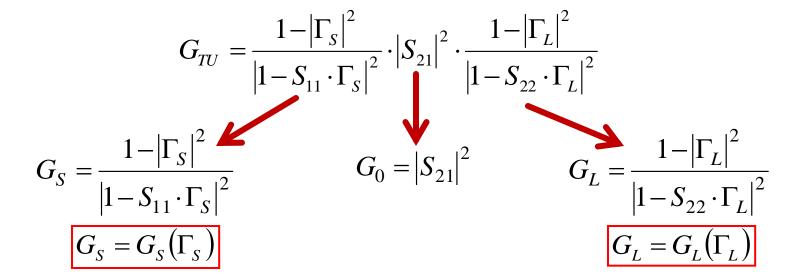
• Usually a transistor suitable for implementing an LNA at a certain frequency will have input gain circles and noise circles in the same area for  $\Gamma_S$ 



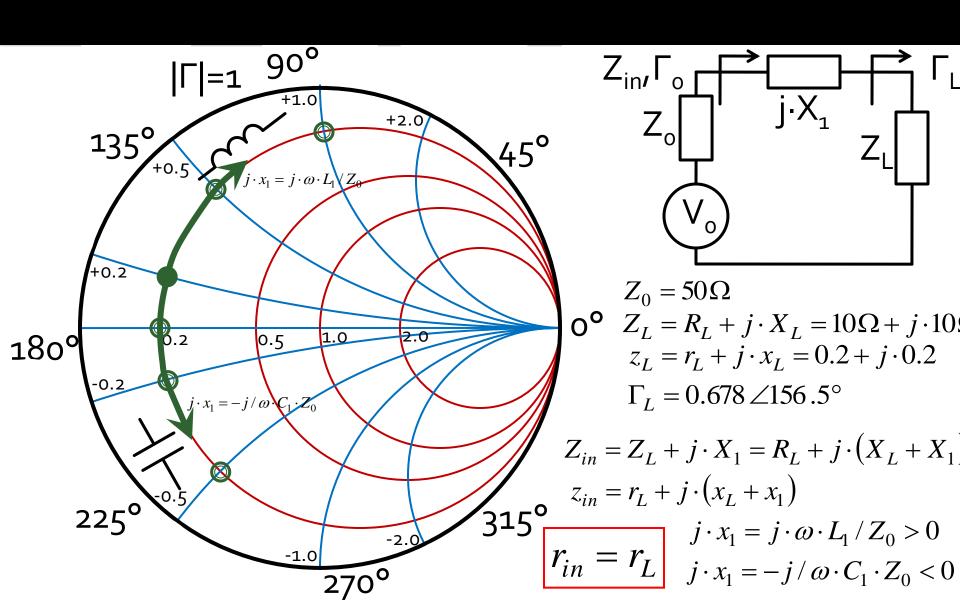
## Design for Specified Gain



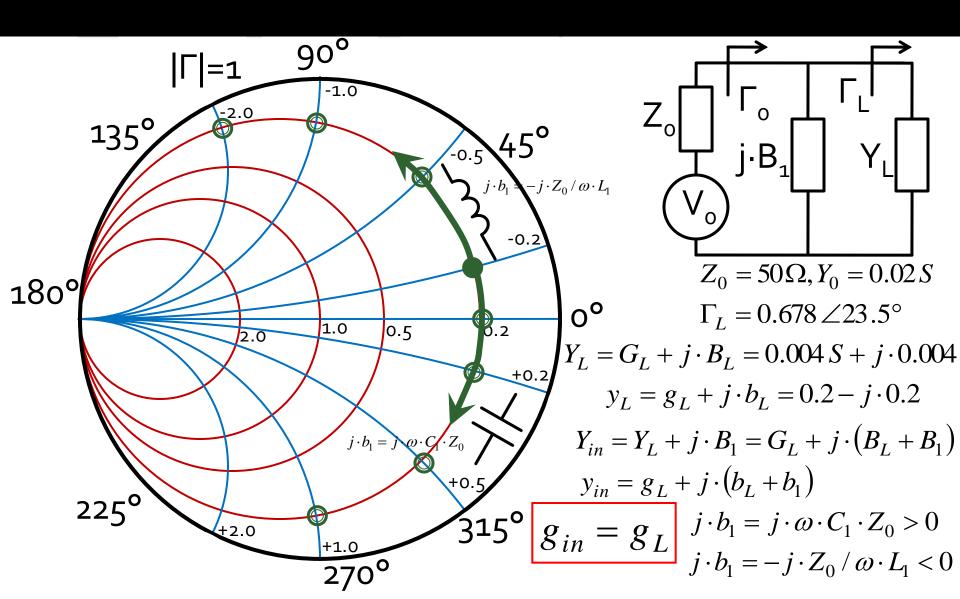
In the unilateral assumption:



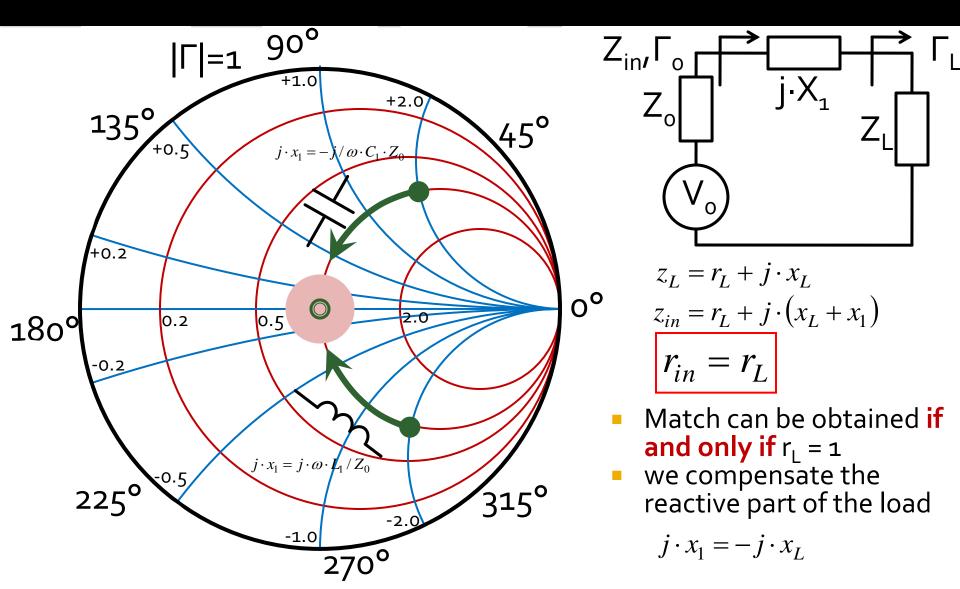
#### The Smith Chart, series reactance



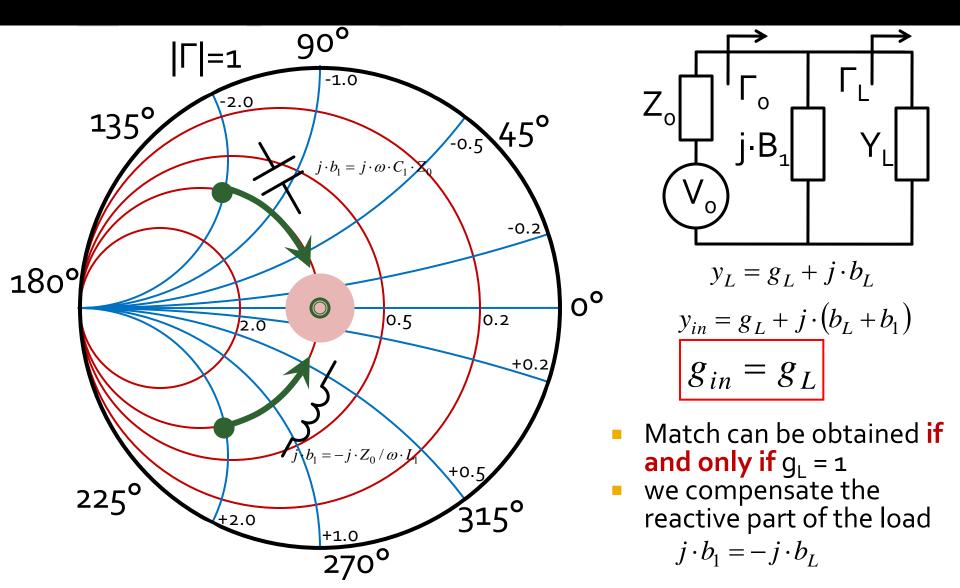
# The Smith Chart, shunt susceptance



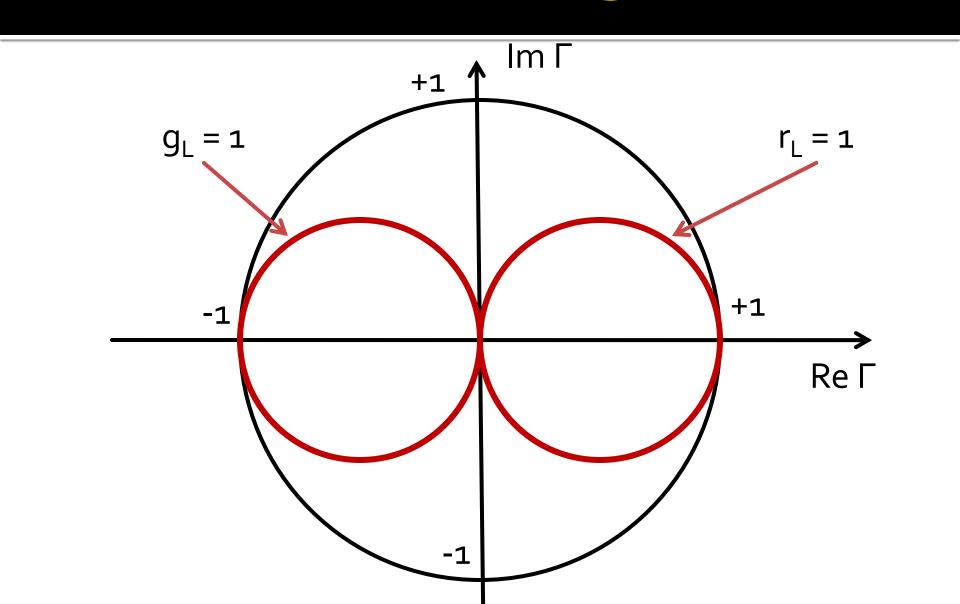
# Matching, series reactance



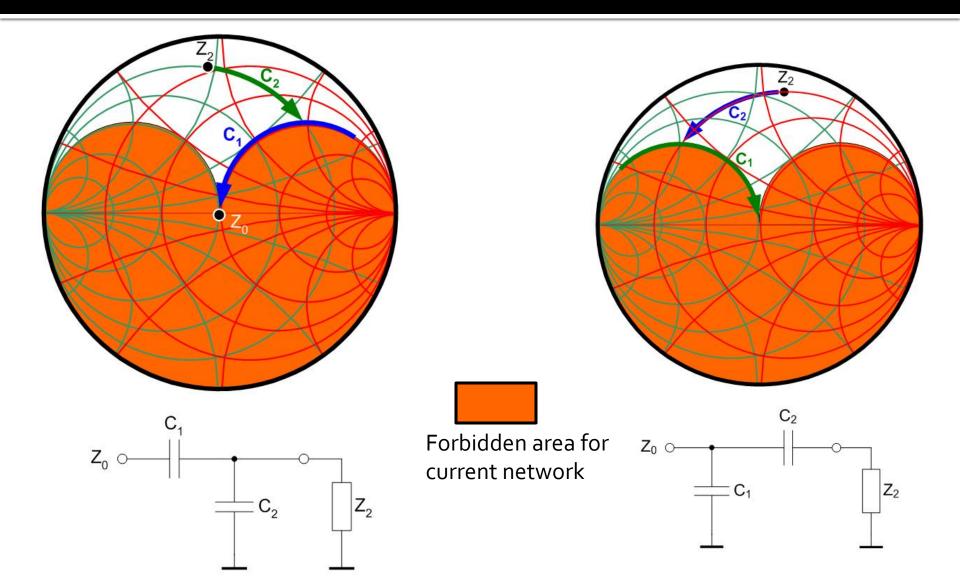
# Matching, shunt susceptance



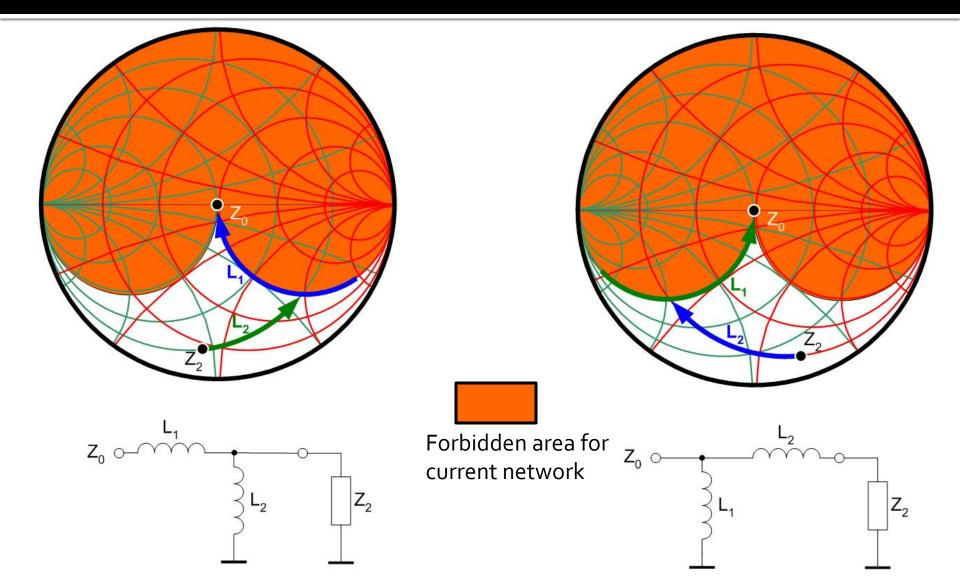
# Smith chart, r=1 and g=1



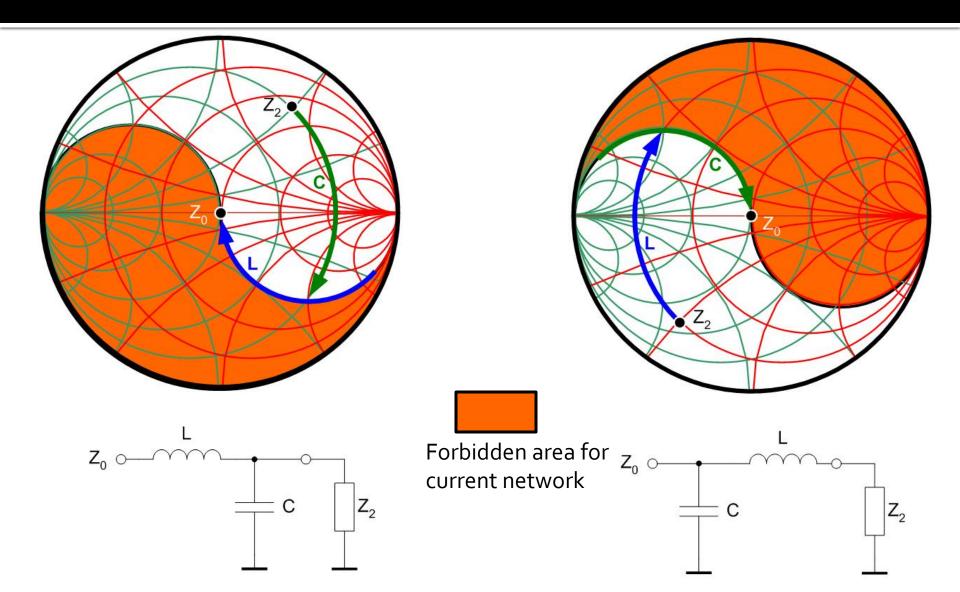
# series C, shunt C / shunt C, series C



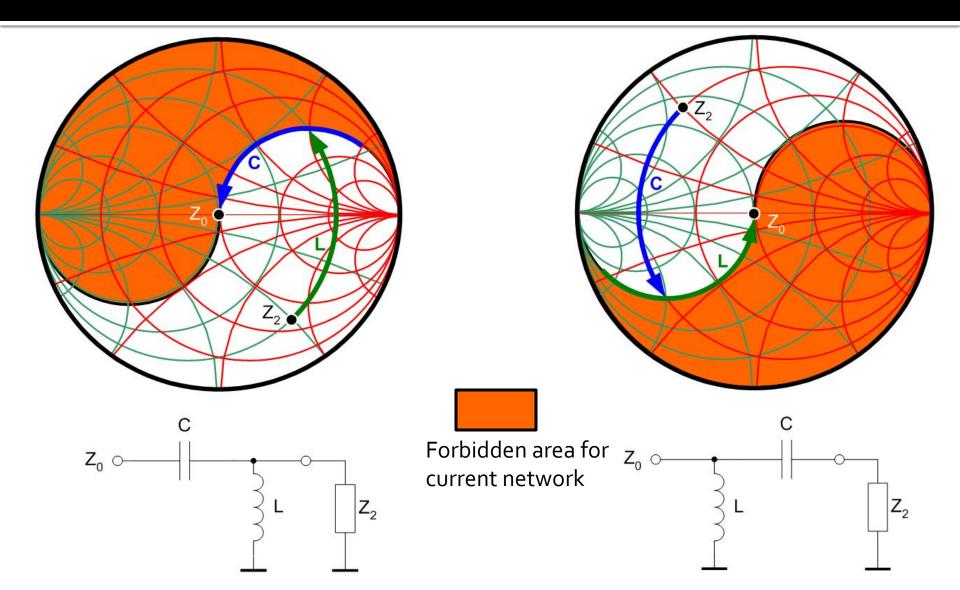
# series L, shunt L / shunt L, series L



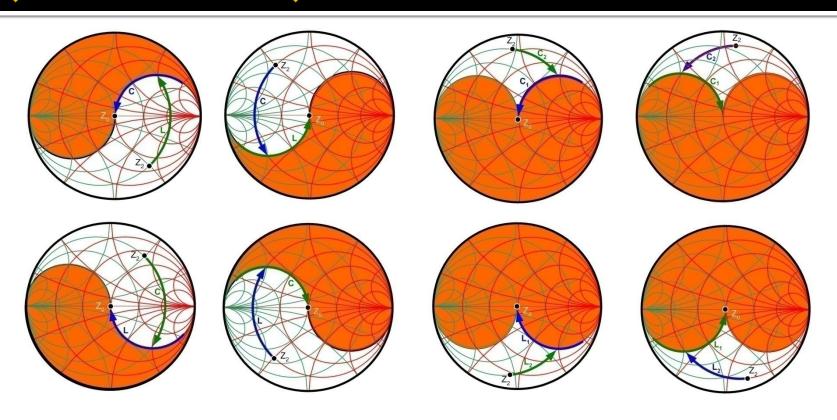
# series L, shunt C / shunt C, series L



# series C, shunt L / shunt L, series C



# Matching with 2 reactive elements (L Networks)





# Matching with 2 reactive elements (L Networks)

- For any Γ<sub>L</sub> there are at least 2 possible L networks to achieve match (L+C)
- For some starting areas on the Smith Chart there are 4 possibilities (+2 C+C/L+L networks)
- We choose the network that requires components with existent/practically realizable values
- By adding the resistive elements, we can supplement the number of networks but with loss of signal power (not recommended)

# **Practical Procedure**

# Step o

Write by hand on a sheet of paper 100 times:

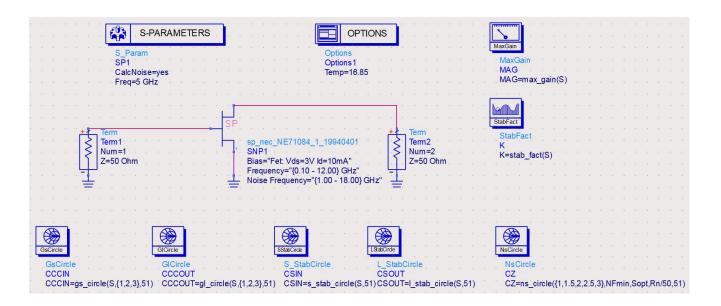
 I solemnly promise to read the text AND NOT to jump from picture to picture



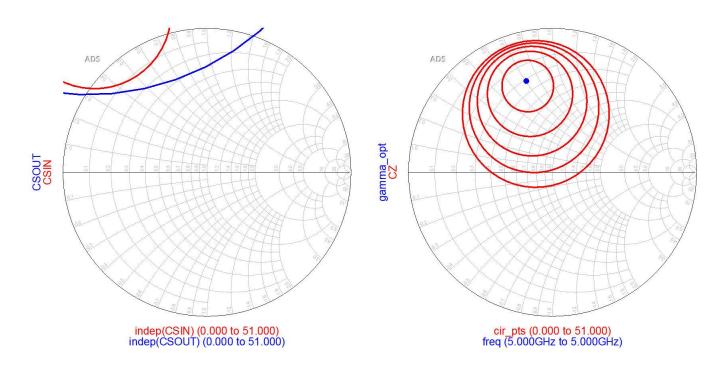
### Step 1

- Laboratory 3-4 will take 2 sessions to complete:
  - lab 3: In the first session you will work with the design data in the example in the lab manual in order to create the 4 (correct) schematics in a single ADS project
  - lab 4: starting from the 4 (verified) schematics to design your amplifier (individual data)
- Caution! the 4 schematics must be saved in the "networks" folder inside the "...\_prj" folder (ADS project) in order to belong to that particular project (and have simulation enabled)

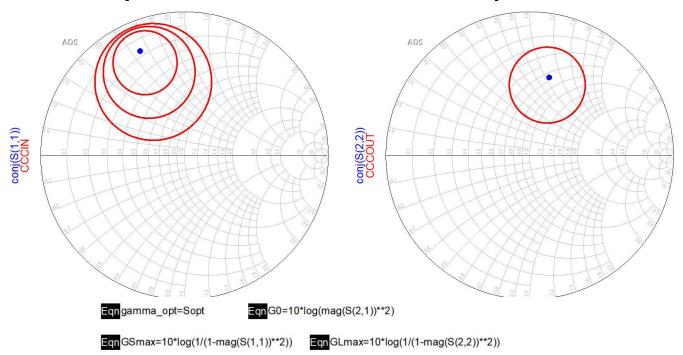
 allows investigation of the transistor at chosen design frequency



 multiple circles (families) are plotted and some required values are computed



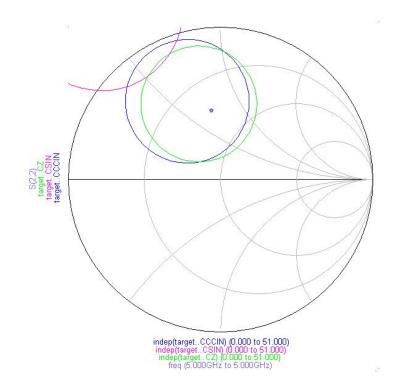
 multiple circles (families) are plotted and some required values are computed



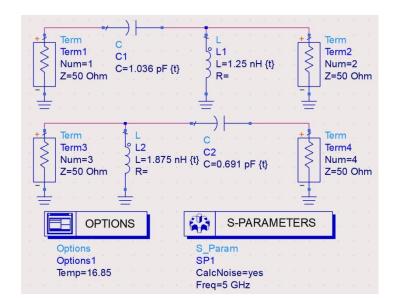
freq	K	MAG	NFmin	Sopt	Rn	G0	GLmax	GSmax
5.000 GHz	0.533	15.296	0.700	0.660 / 106	19.500	8.974	1.634	4.249

- Largely similar with schematic 1
- Analyzing results in schematic 1 we choose a single circle adequate as target:
  - stability
  - power gain
  - noise (input)
- Plotting these circles is not required
  - they will be effectively used in schematic 3

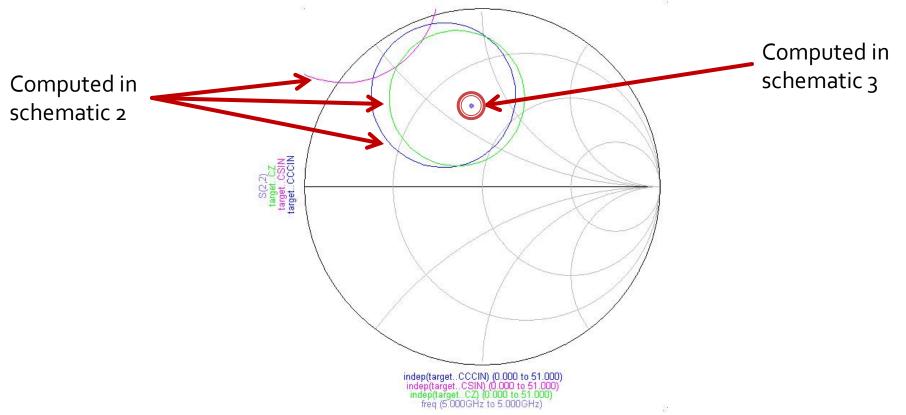
 Even if the circles are not plotted, they must be computed (by simulation of schematic 2)



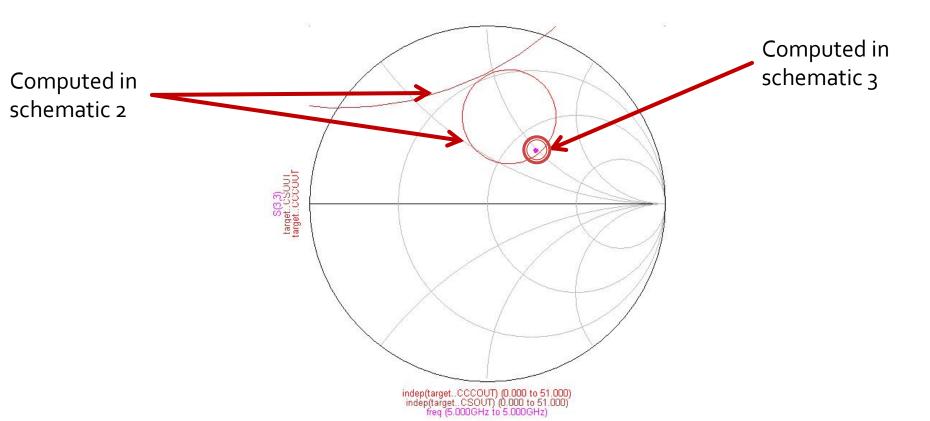
- Uses circles computed in schematic 2 as target
- Tune the components in the two L networks to reach the desired points



 Tune the components in the two L networks to reach the desired points

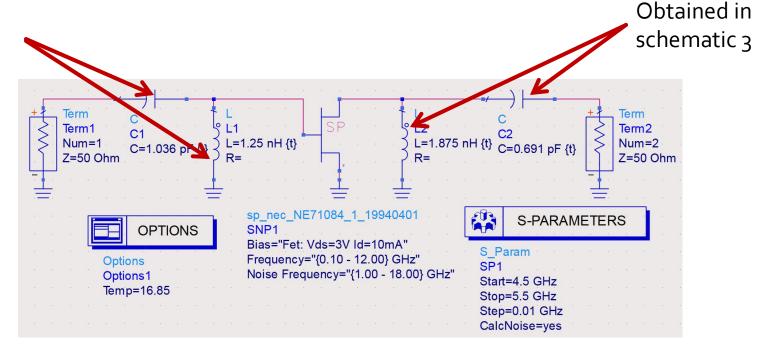


 Tune the components in the two L networks to reach the desired points

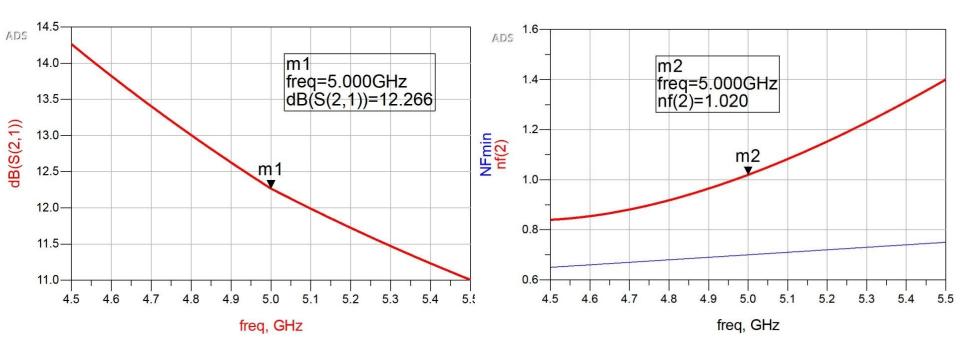


 Insert the components obtained by tuning in schematic 3 as input/output matching networks for the transistor

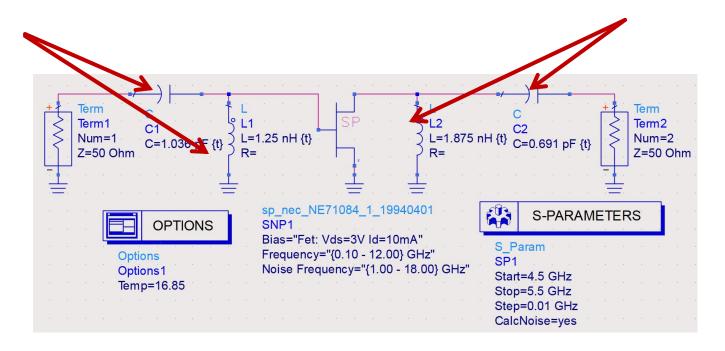
Obtained in schematic 3



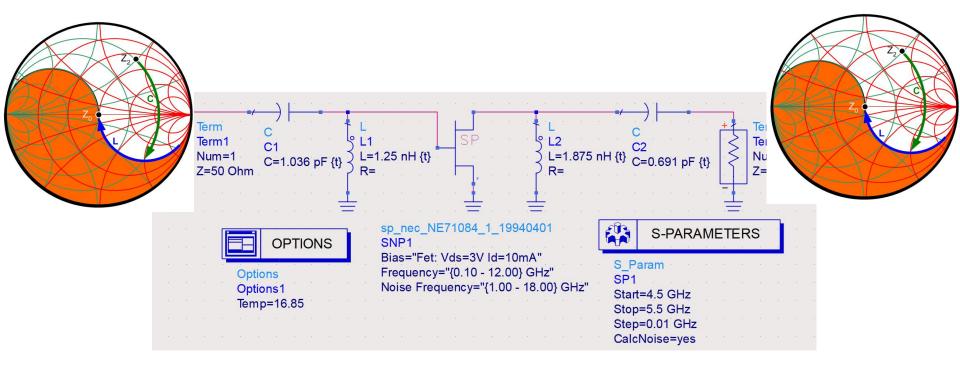
Initial results, probably good but not perfect



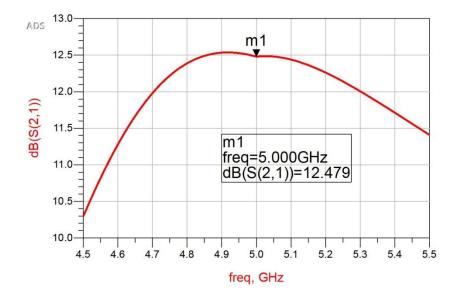
 Tune the components in the input/output matching networks for better results



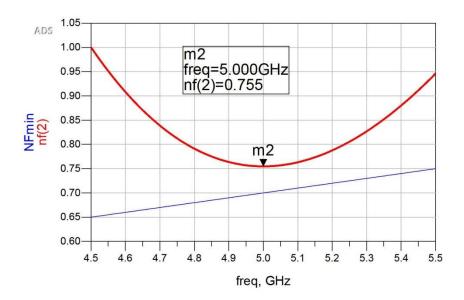
 Tuning directly in schematic 4 (without passing through the other 3 schematics) has zero chances of success



- We obtain (after tuning) the final values and check the fulfillment of the design data:
  - Power gain



- We obtain (after tuning) the final values and check the fulfillment of the design data:
  - Noise factor



#### Contact

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- http://rf-opto.etti.tuiasi.ro
- rdamian@etti.tuiasi.ro